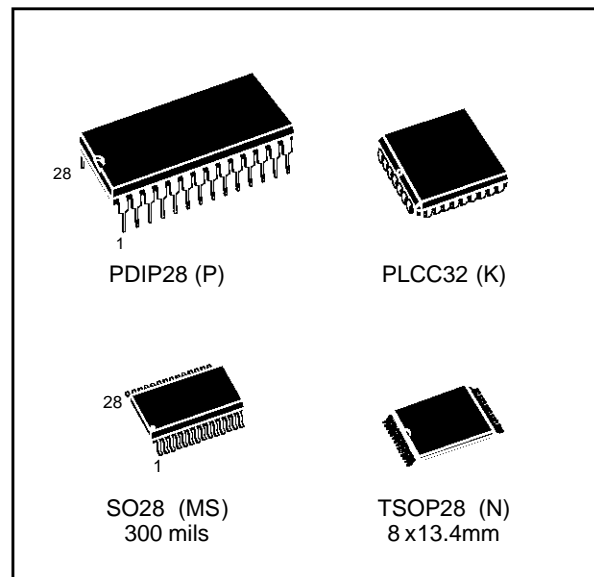


LOW VOLTAGE PARALLEL 64K (8K x 8) EEPROM WITH SOFTWARE DATA PROTECTION

DATA BRIEFING

- FAST ACCESS TIME: 200ns
- SINGLE LOW VOLTAGE OPERATION
- LOW POWER CONSUMPTION
- FAST WRITE CYCLE:
 - 64 Bytes Page Write Operation
 - Byte or Page Write Cycle: 3ms Max
- ENHANCED END OF WRITE DETECTION:
 - Ready/Busy Open Drain Output (only on the M28LV64)
 - Data Polling
 - Toggle Bit
- PAGE LOAD TIMER STATUS BIT
- HIGH RELIABILITY SINGLE POLYSILICON, CMOS TECHNOLOGY:
 - Endurance >100,000 Erase/Write Cycles
 - Data Retention >40 Years
- JEDEC APPROVED BYTEWIDE PIN OUT
- SOFTWARE DATA PROTECTION



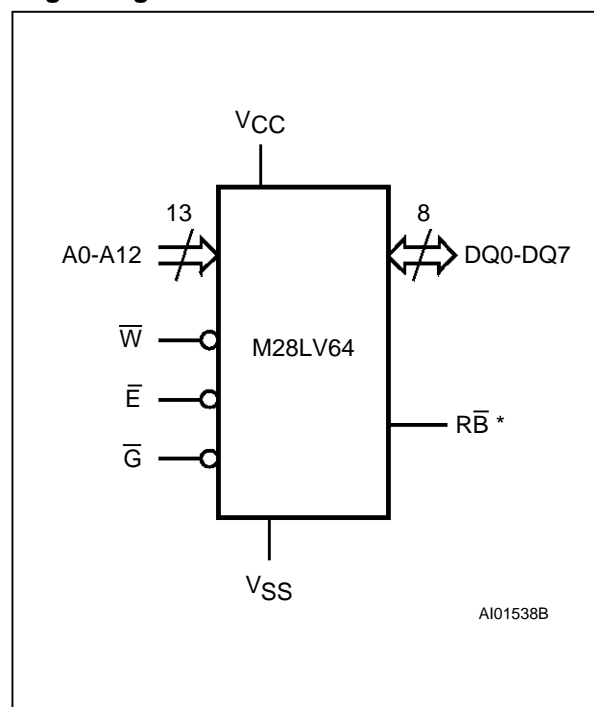
DESCRIPTION

The M28LV64 is an 8K x 8 low power Parallel EEPROM fabricated with SGS-THOMSON proprietary single polysilicon CMOS technology. The device offers fast access time with low power dissipation and requires a 2.7V to 3.6V power supply.

Signal Names

A0 - A12	Address Input
DQ0 - DQ7	Data Input / Output
\bar{W}	Write Enable
\bar{E}	Chip Enable
\bar{G}	Output Enable
\bar{RB}	Ready / Busy
V _{CC}	Supply Voltage
V _{SS}	Ground

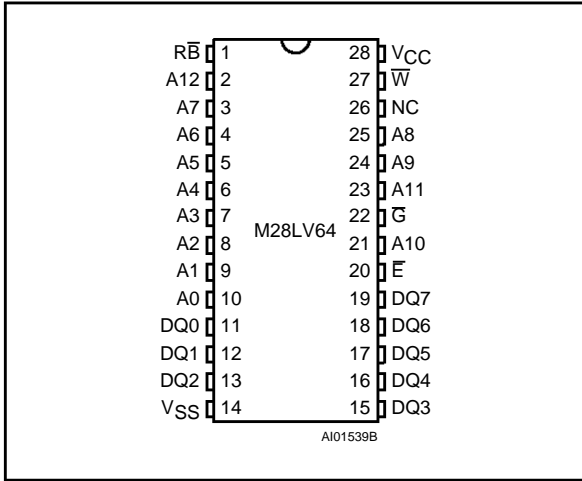
Logic Diagram



Note: * \bar{RB} function is only available on the M28LV64.

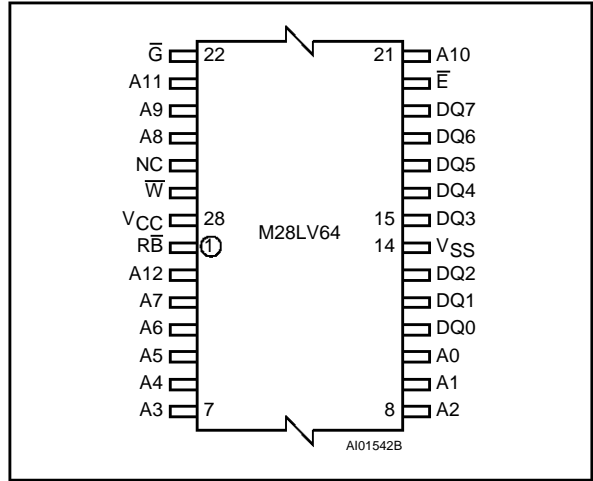
M28LV64

DIP Pin Connections



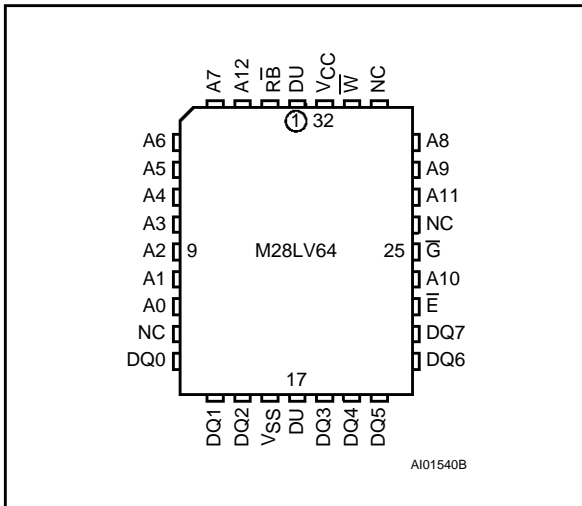
Warning: NC = Not Connected.

TSOP Pin Connections



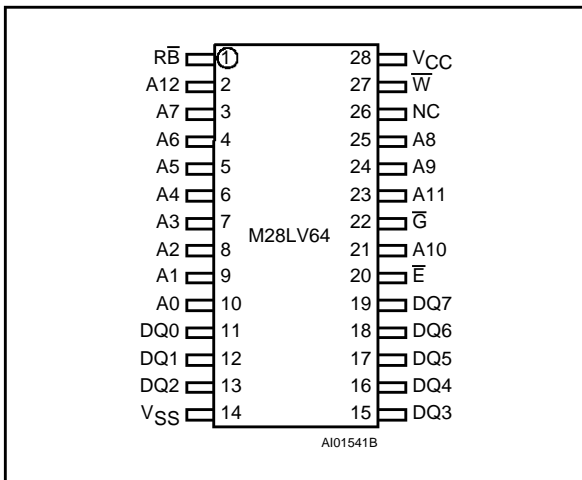
Warning: NC = Not Connected.

LCC Pin Connections



Warning: NC = Not Connected, DU = Don't Use.

SO Pin Connections



Warning: NC = Not Connected.

Ordering Information Scheme

For a list of available options refer to the current Memory Shortform catalogue.

For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

Example: M28LV64 -200 X K 1

Speed	-200	X	K	1
-200	200ns			
-250	250ns			
-300	300ns			
Write Monitoring				
blank	RB function active			
X	No RB function			
Package				
P	PDIP28			
K	PLCC32			
MS	SO28 300mils			
N	TSOP28 8 x 13.4mm			
Temp. Range				
1	0 to 70 °C			
6	-40 to 85 °C			